

FIG.1A

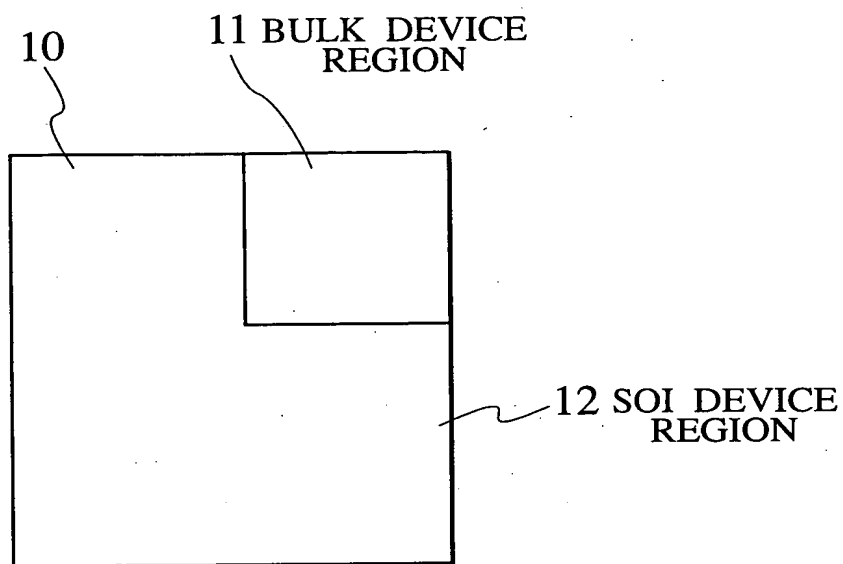


FIG.1B

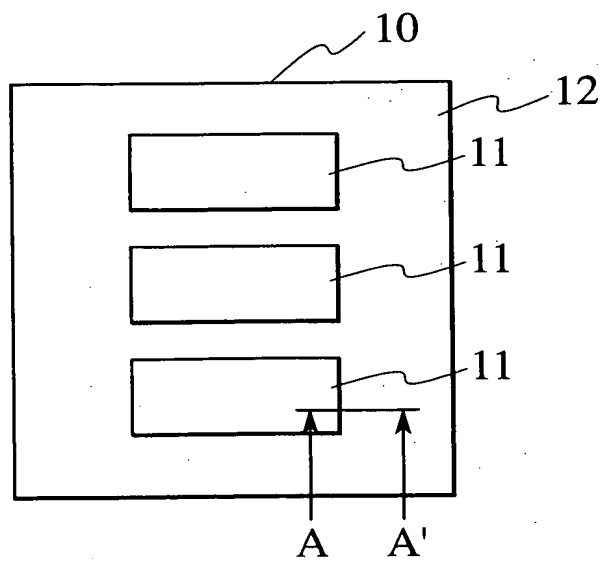


FIG. 2

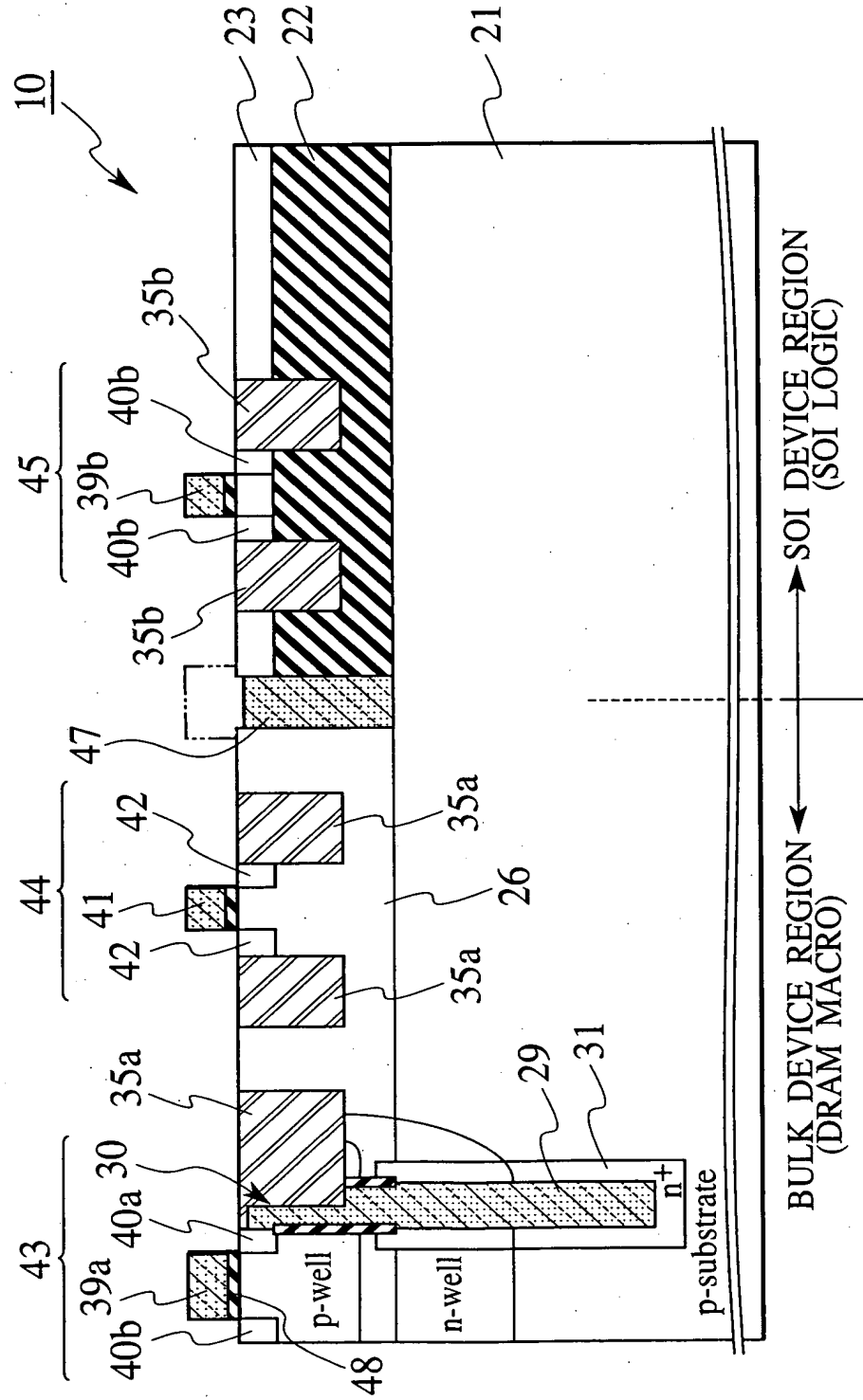


FIG.3A

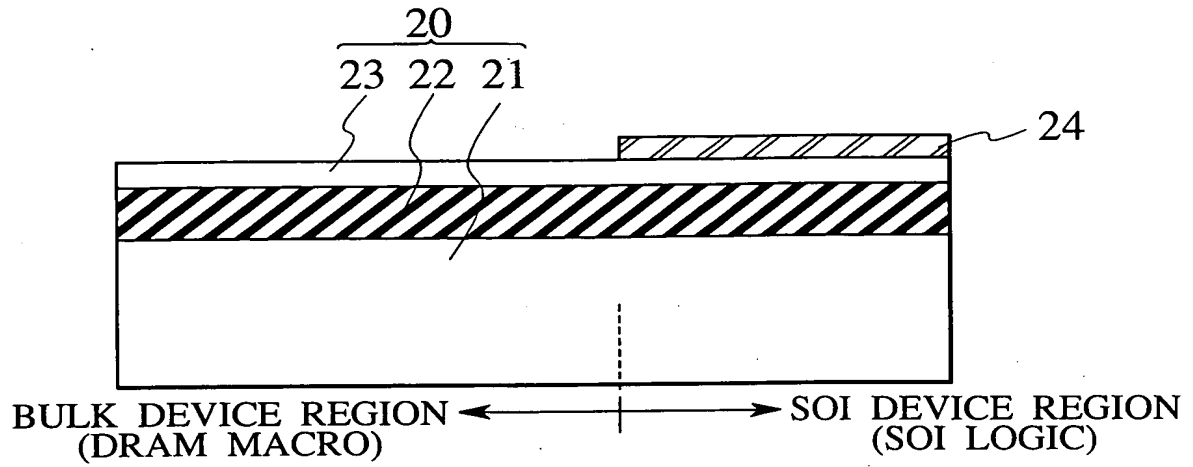


FIG.3B

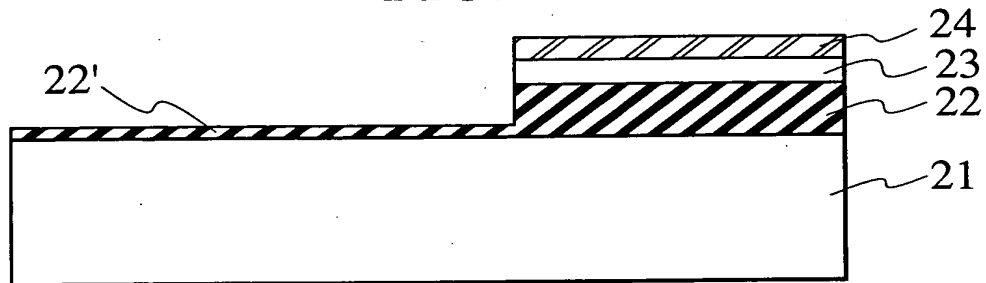


FIG.3C

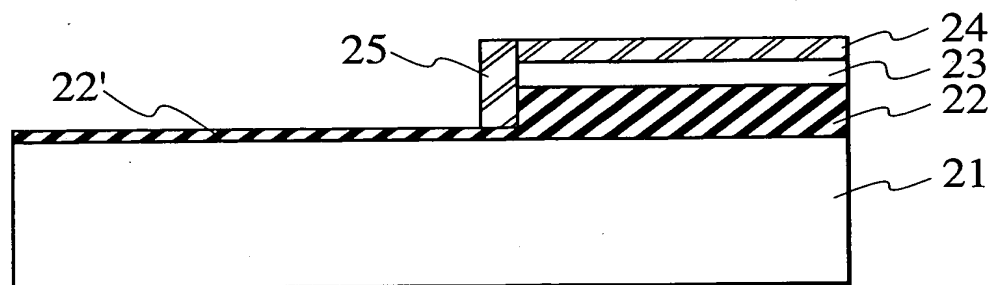


FIG.3D

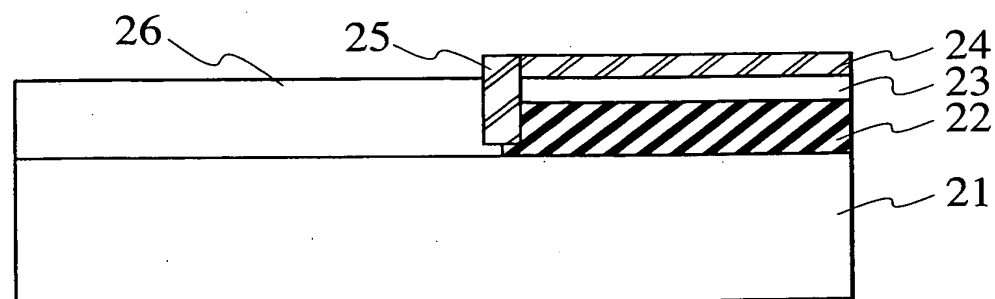


FIG.3E

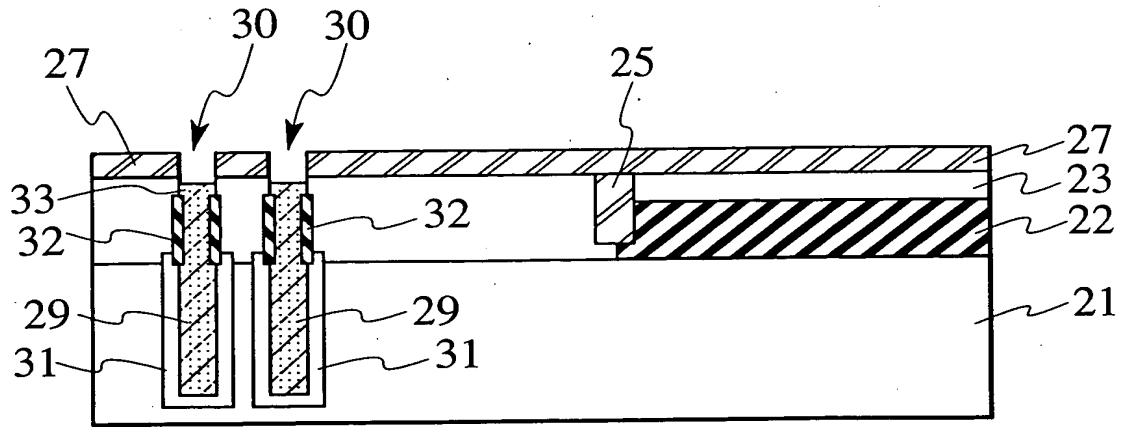


FIG.3F

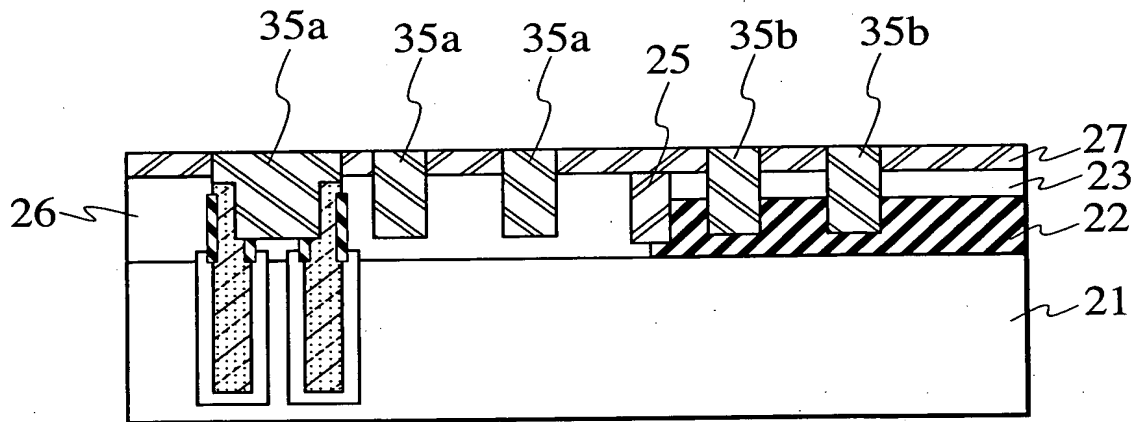


FIG.3G

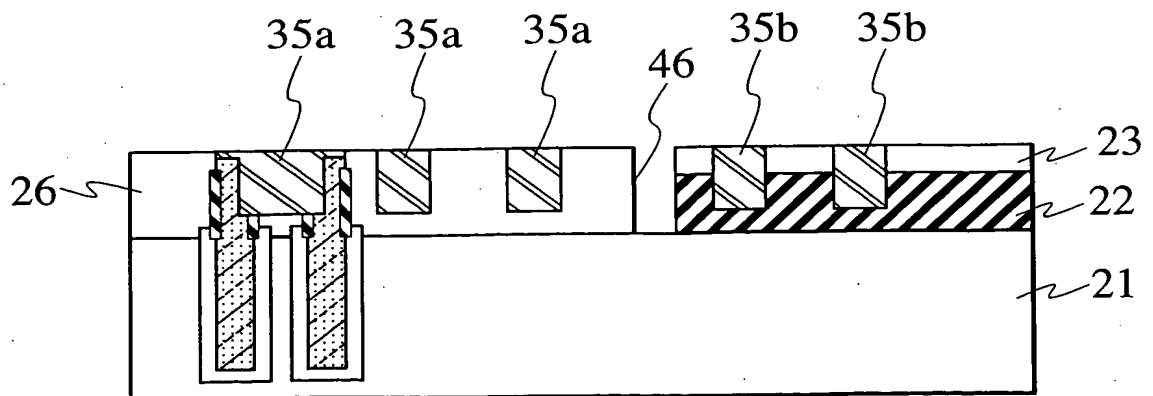


FIG.4

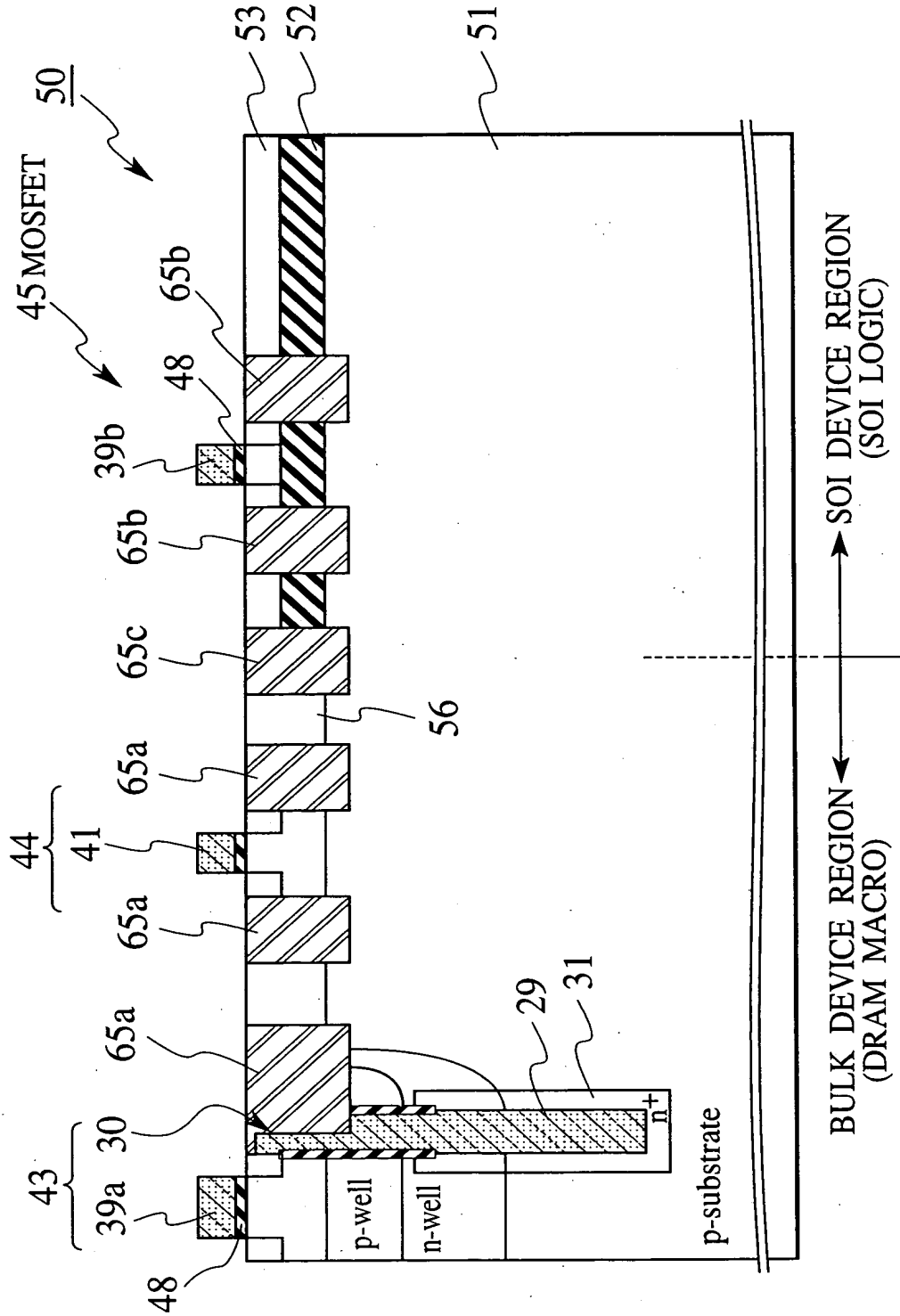


FIG.5A

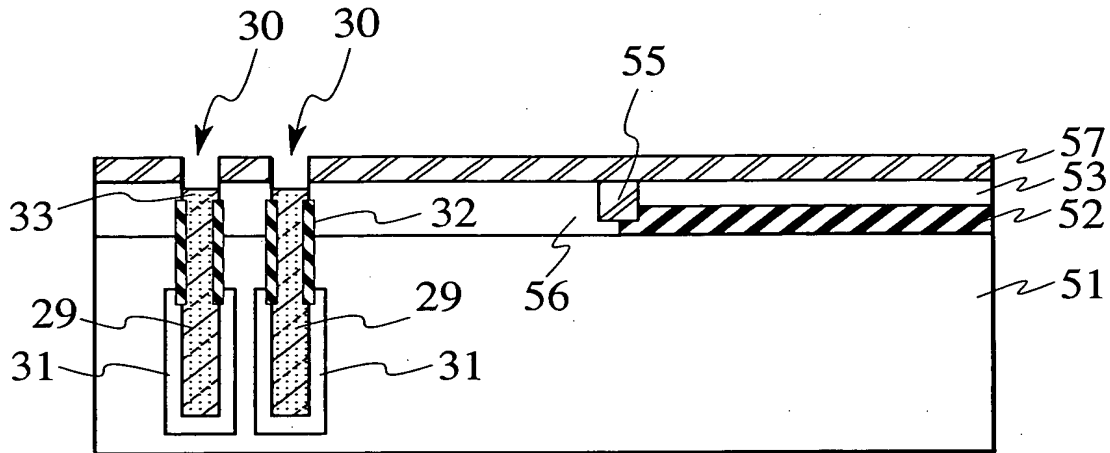


FIG.5B

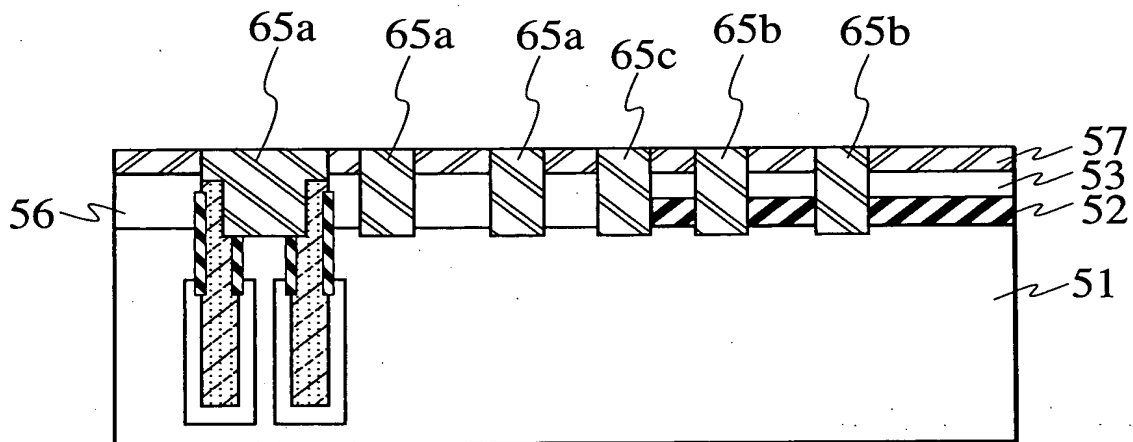


FIG.5C

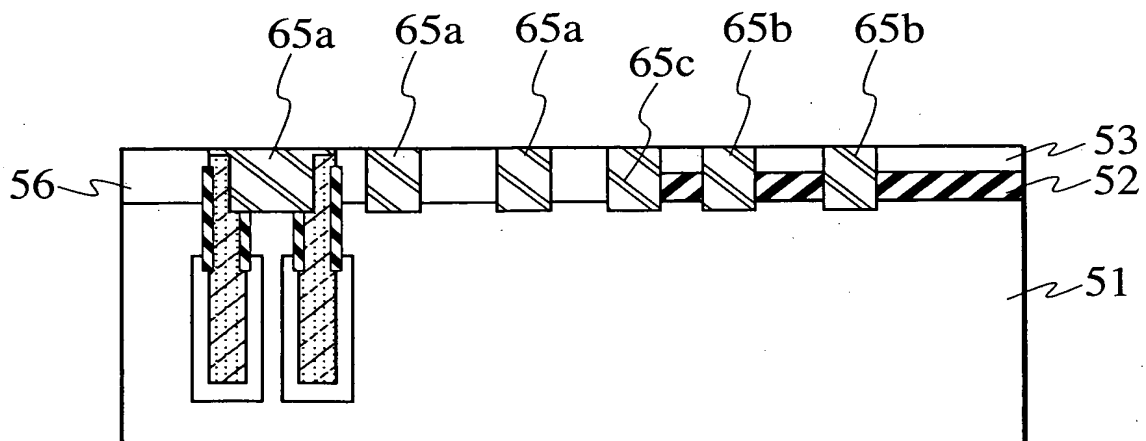


FIG.6

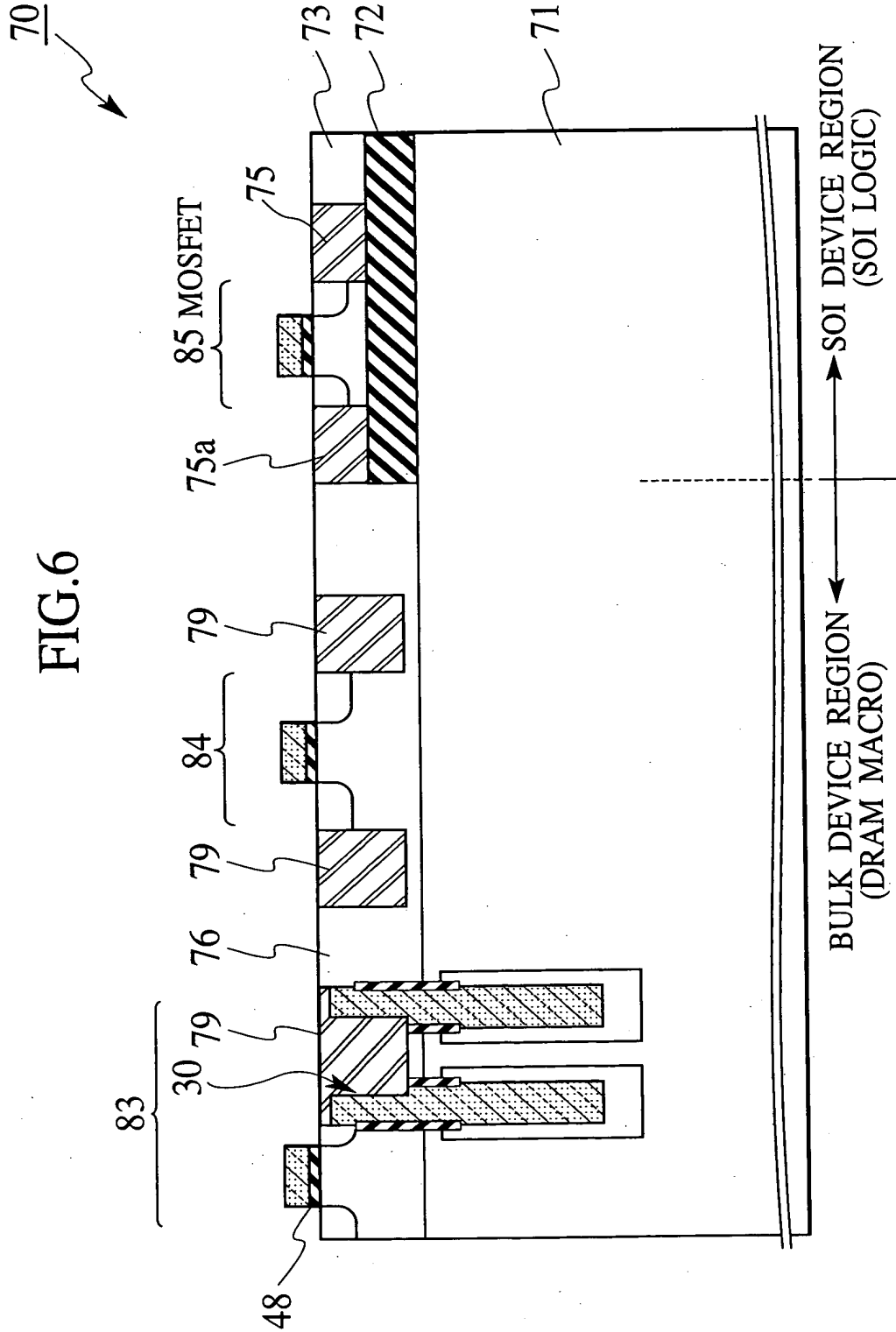


FIG.7A

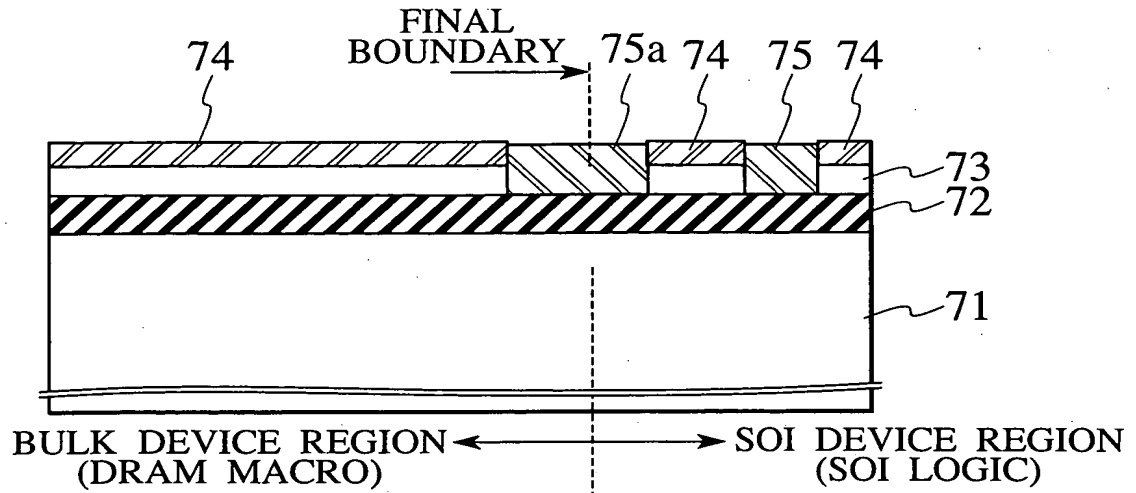


FIG.7B

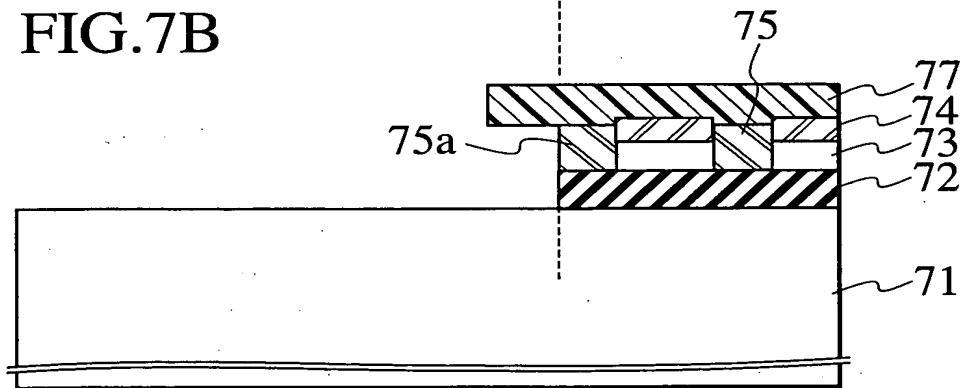


FIG.7C

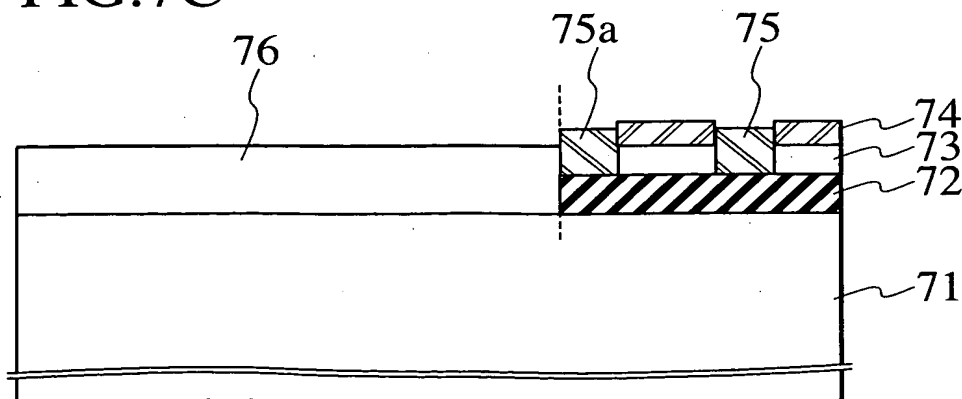


FIG. 7D

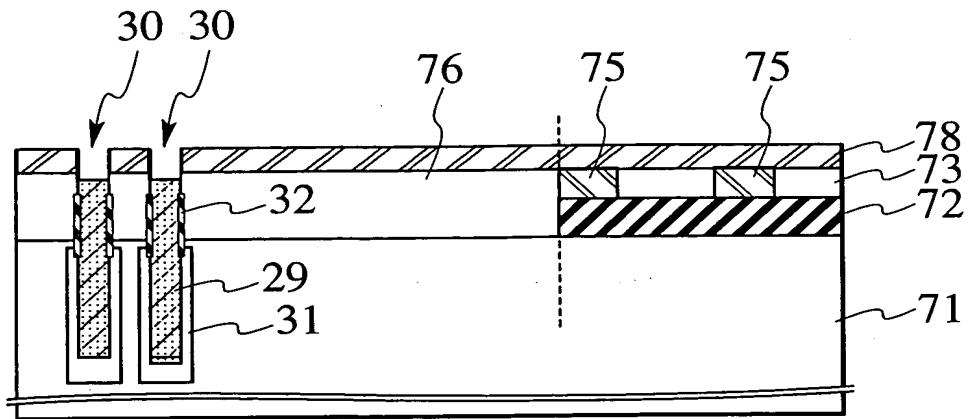


FIG. 7E

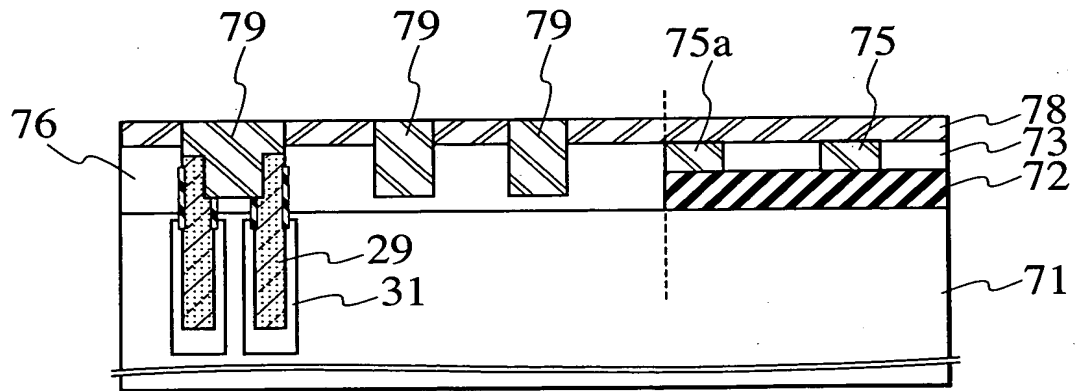


FIG. 7F

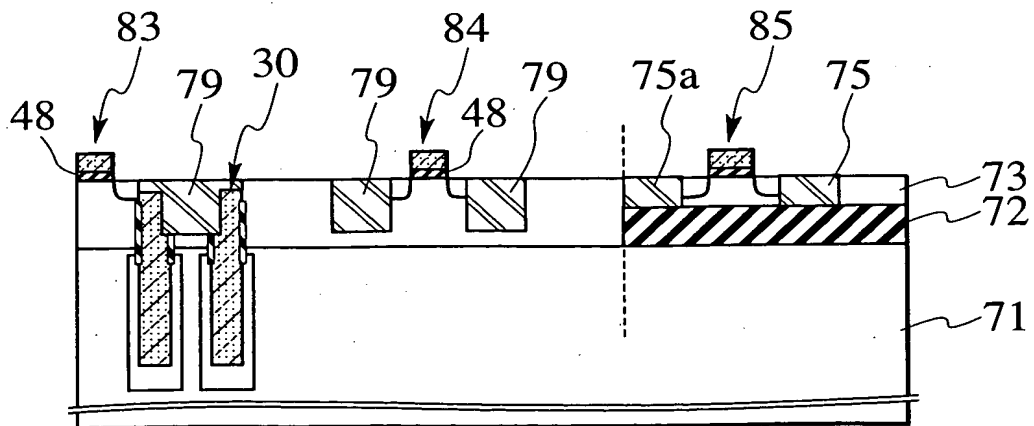


FIG.8A

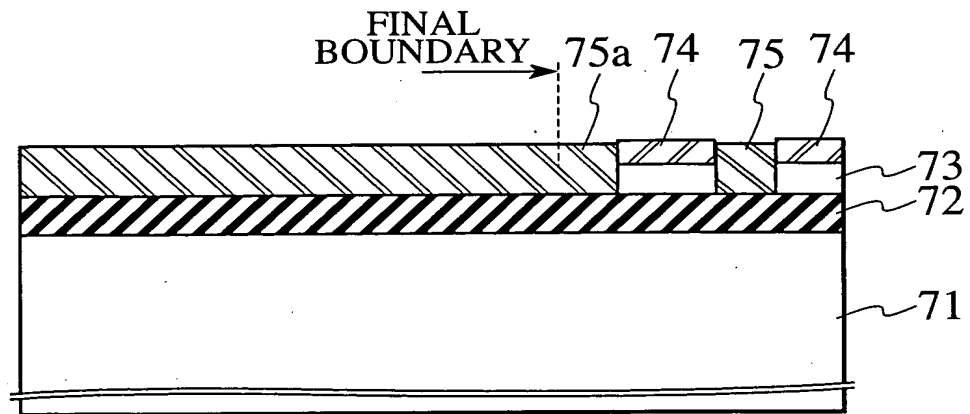


FIG.8B

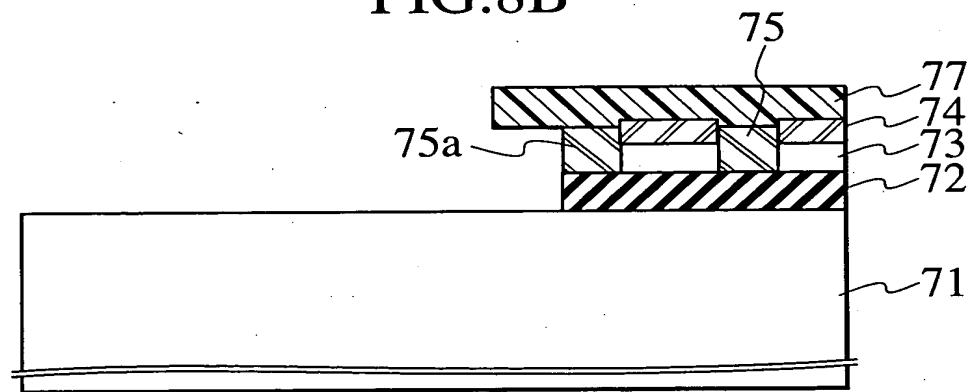
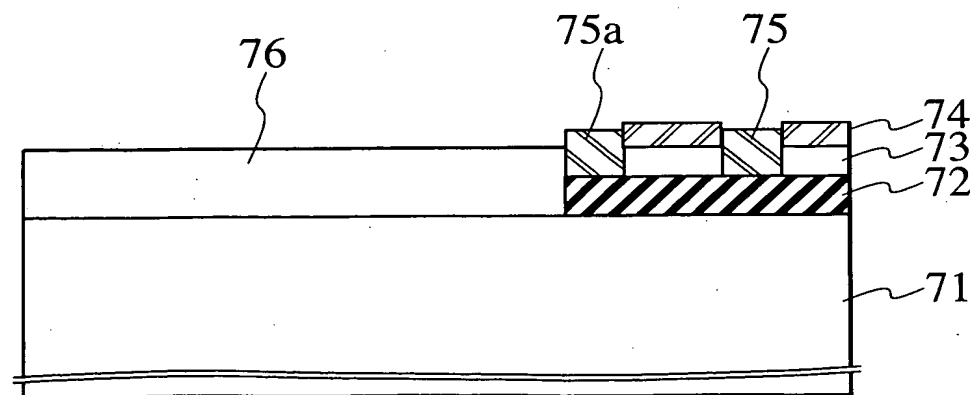


FIG.8C



The diagram illustrates a cross-sectional view of a semiconductor device, divided into two main regions by a vertical dashed line:

- BULK DEVICE REGION (DRAM MACRO):** This region on the left contains a p-well, an n-well, and an n+ region. A vertical structure is labeled 29, and a horizontal structure is labeled 31. The p-substrate is at the base.
- SOI DEVICE REGION (SOI LOGIC):** This region on the right contains a MOSFET structure. The gate stack is labeled 45. The channel region is labeled 48. The source and drain regions are labeled 97b. The gate is labeled 97c. The gate oxide is labeled 94. The gate oxide is also labeled 39a and 30. The gate oxide is also labeled 39b and 41. The gate oxide is also labeled 96. The gate oxide is also labeled 93 and 92. The gate oxide is also labeled 91.

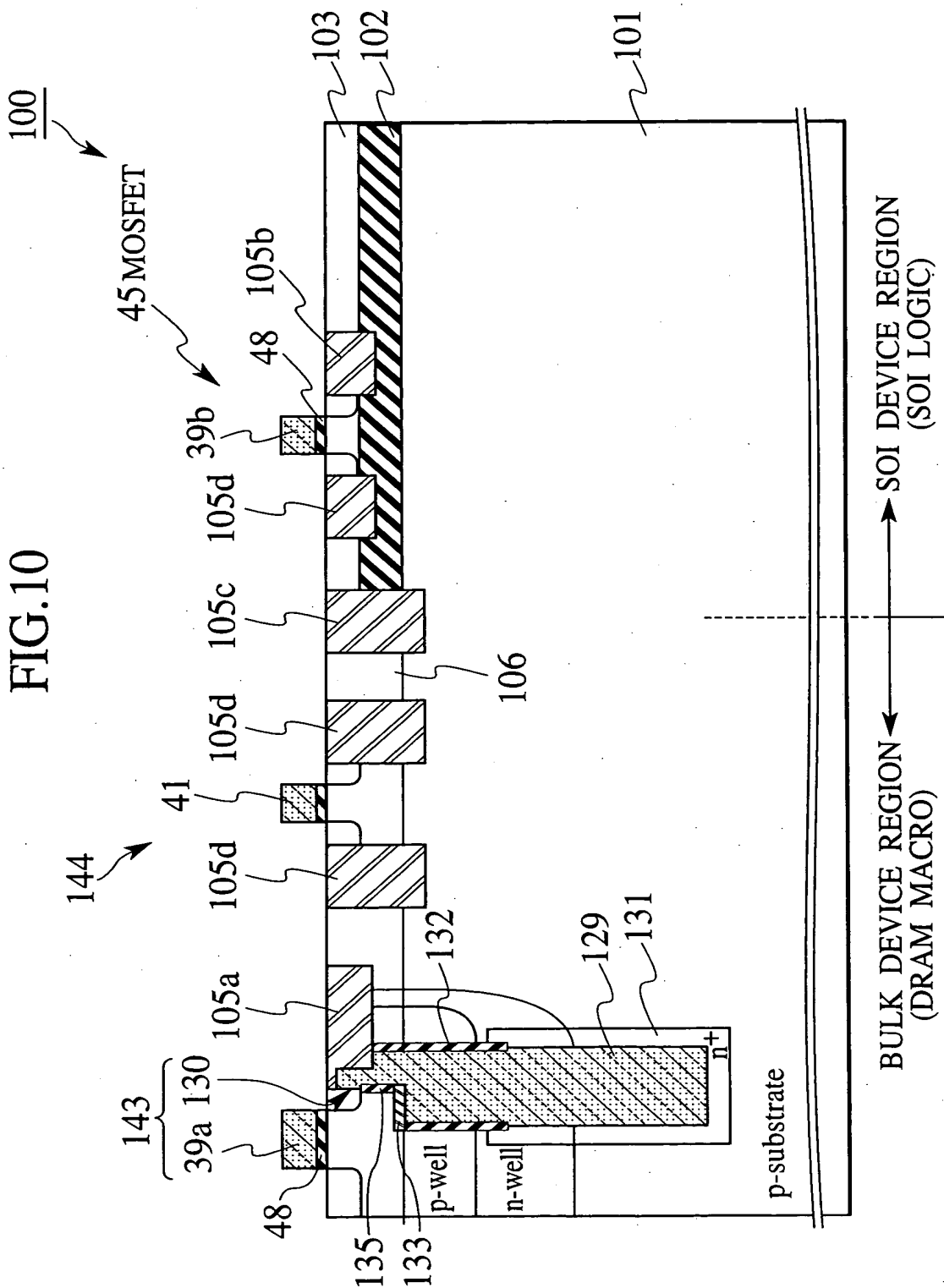


FIG.11A

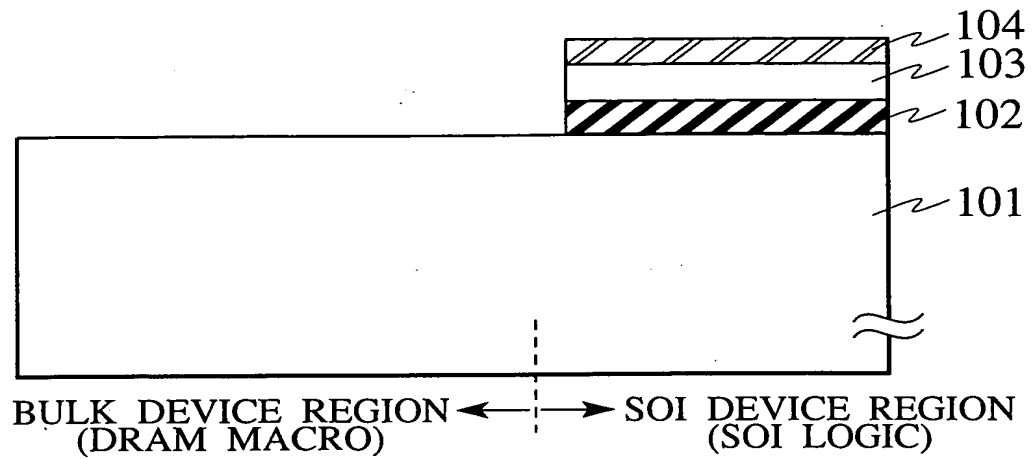


FIG.11B

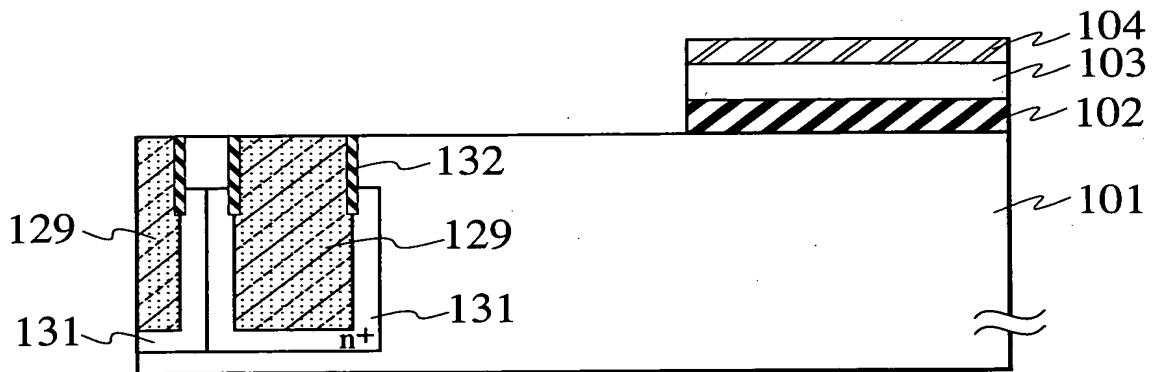
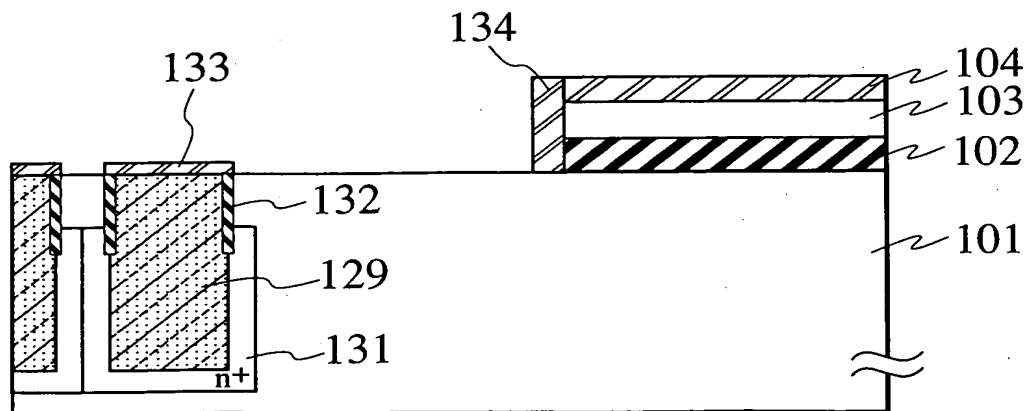
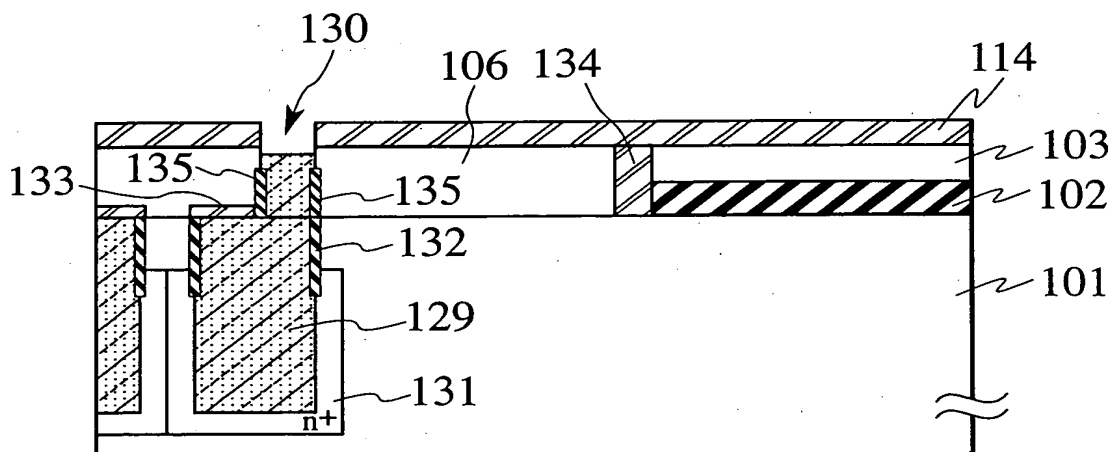
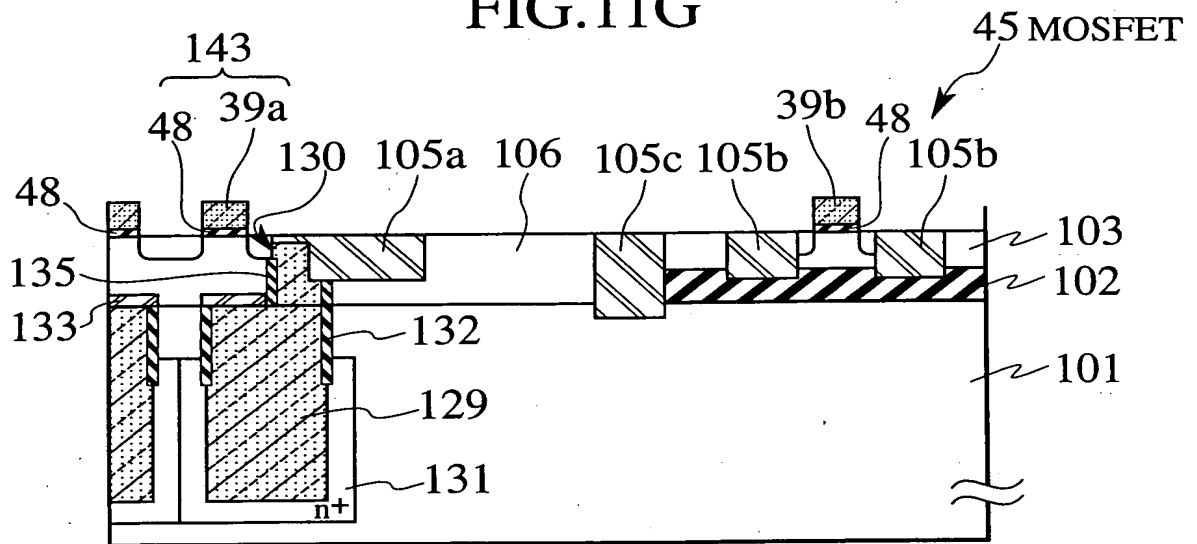


FIG.11C







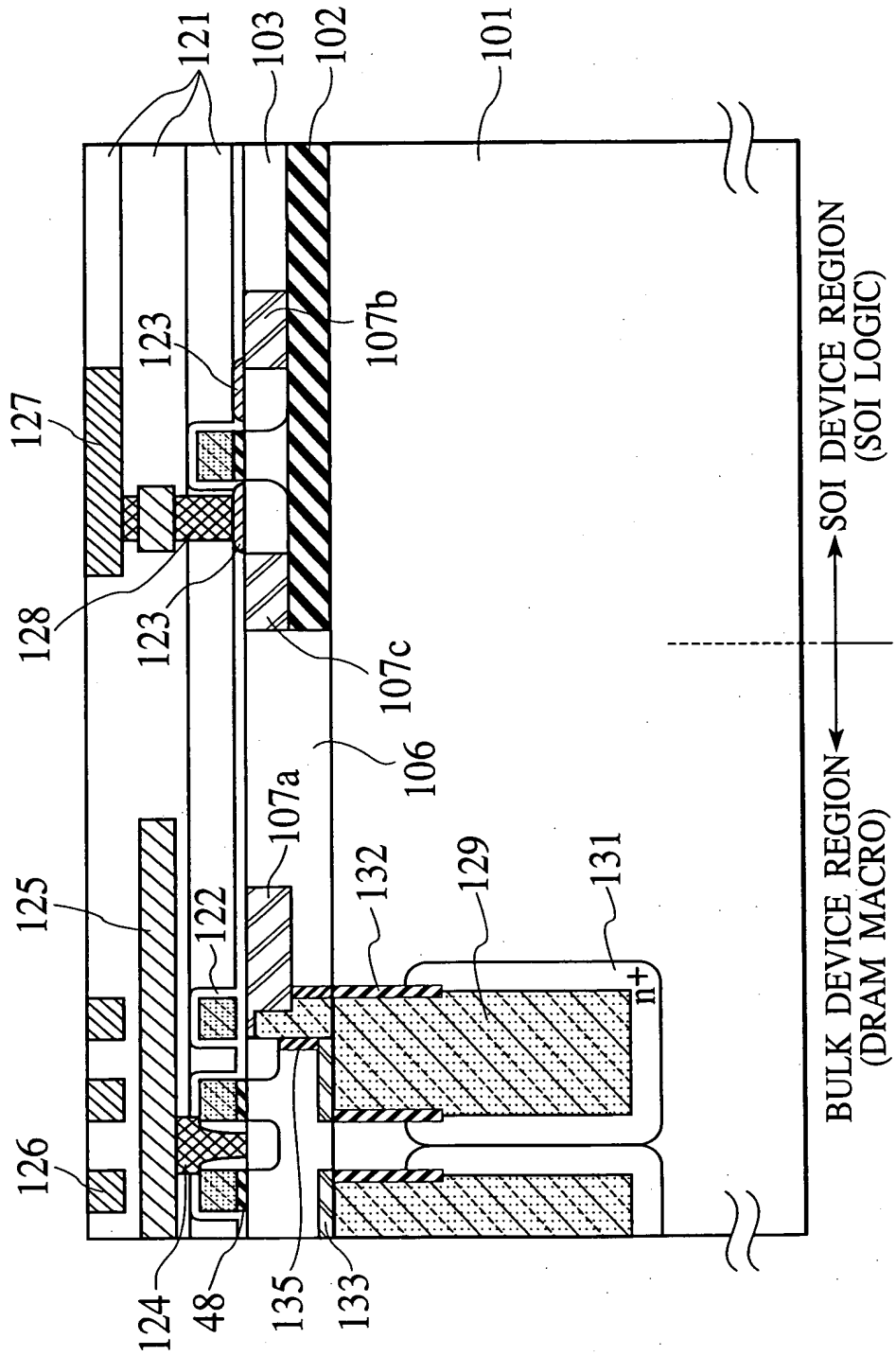


FIG.13

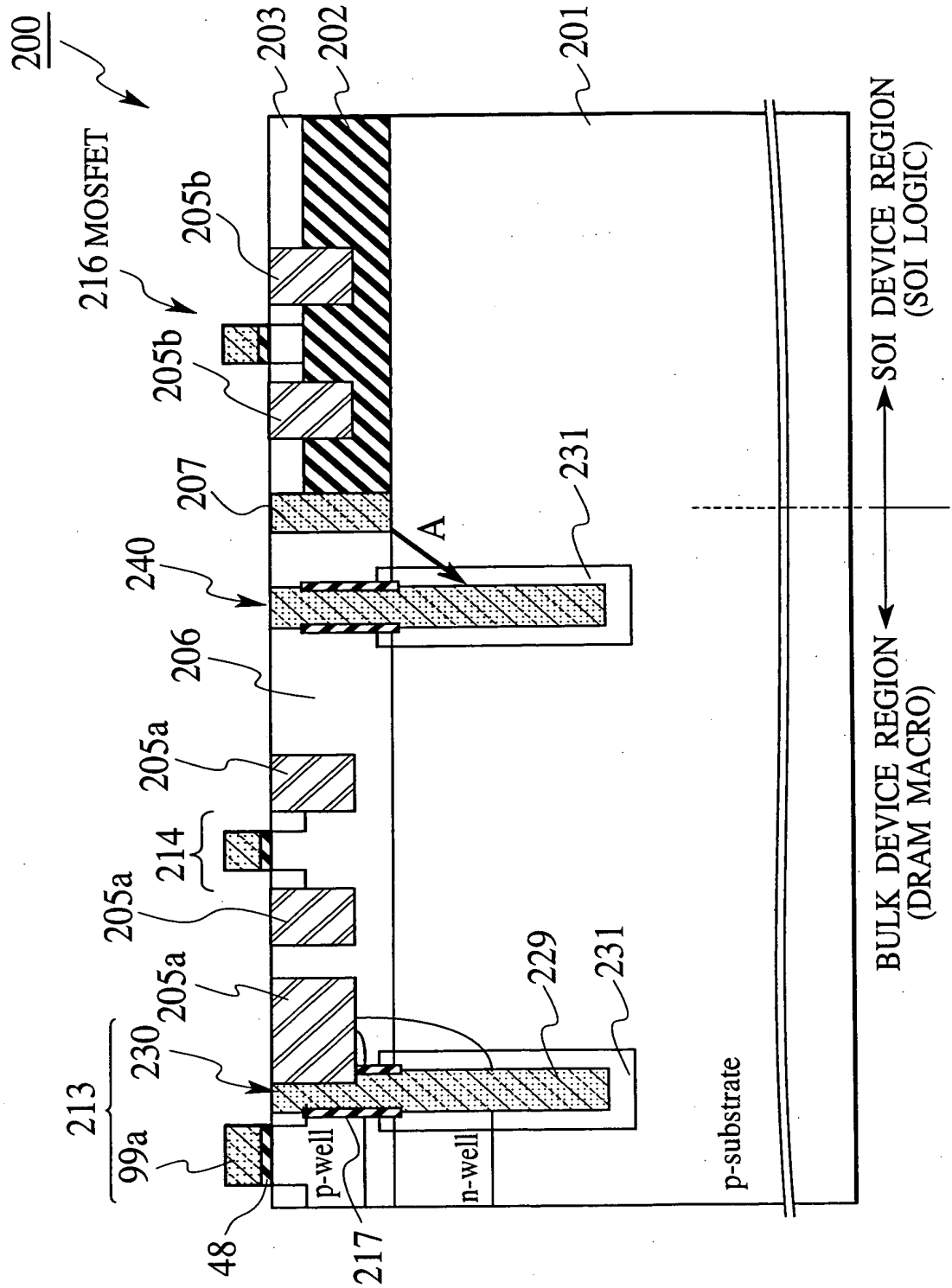


FIG.14

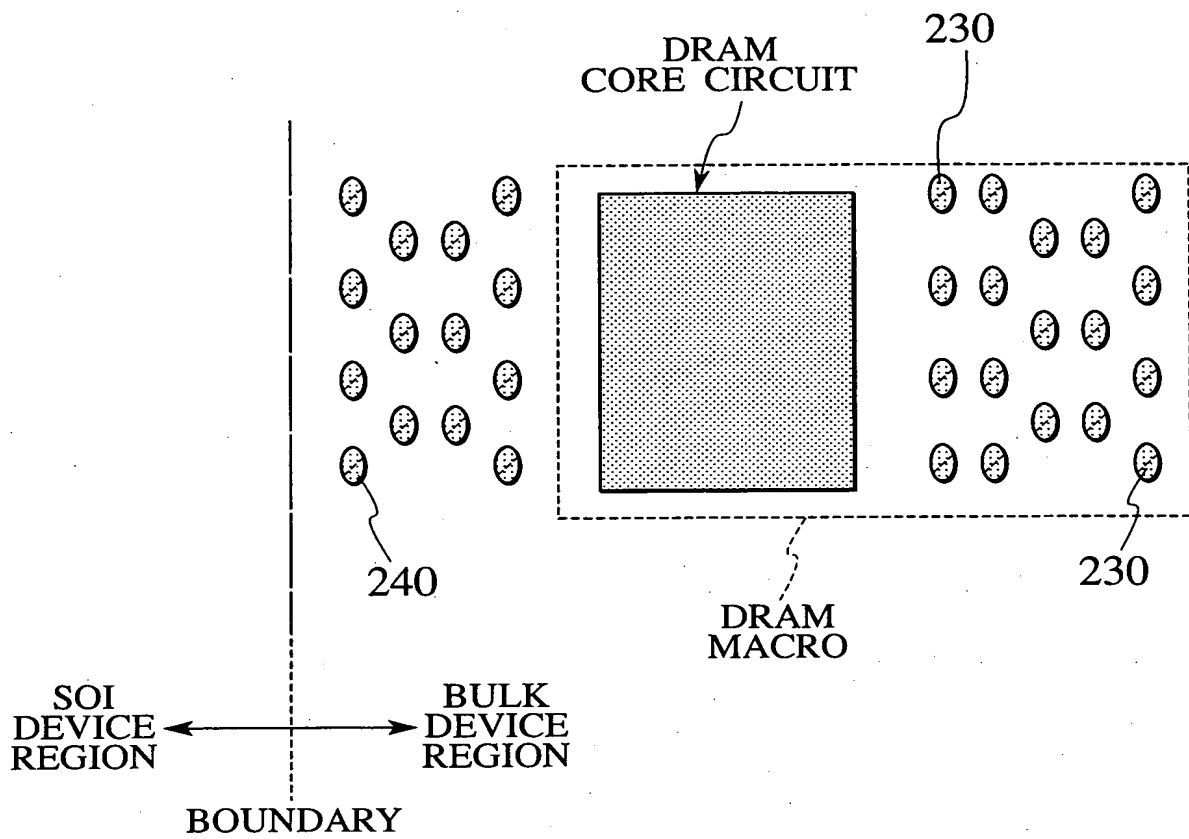


FIG.15A

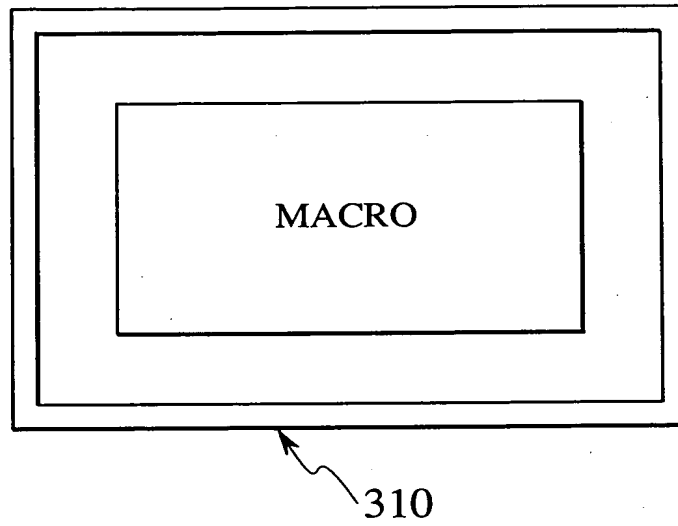


FIG.15B

